

ZXMN2F34FH

20V SOT23 N-channel enhancement mode MOSFET



Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ (Ω)	I_D (A)
20	0.060 @ $V_{GS} = 4.5V$	4.0
	0.120 @ $V_{GS} = 2.5V$	2.9

Description

This new generation Trench MOSFET from TY features low on-resistance achievable with low (2.5V) gate drive.

Features

- Low on-resistance
- 2.5V gate drive capability
- SOT23 package

Applications

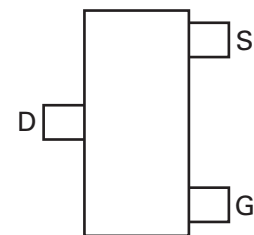
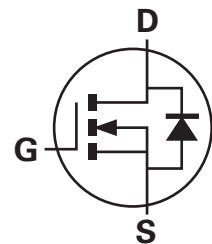
- Buck/Boost DC-DC Converters
- Motor Control
- LED Lighting

Ordering information

DEVICE	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN2F34FHTA	7	8	3000

Device marking

KNB



Top view

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Drain source voltage	V_{DSS}	20	V
Gate source voltage	V_{GS}	± 12	V
Continuous Drain Current @ $V_{GS}=4.5$; $T_A=25^{\circ}\text{C}^{(b)}$ @ $V_{GS}=4.5$; $T_A=70^{\circ}\text{C}^{(b)}$ @ $V_{GS}=4.5$; $T_A=25^{\circ}\text{C}^{(a)}$	I_D	4.0	A
		3.3	A
		3.4	A
Pulsed drain current ^(c)	I_{DM}	18.6	A
Continuous source current (body diode) ^(b)	I_S	2.1	A
Pulsed source current (body diode) ^(c)	I_{SM}	18.6	A
Power dissipation at $T_A=25^{\circ}\text{C}^{(a)}$	P_D	0.95	W
Linear derating factor		7.6	mW/ $^{\circ}\text{C}$
Power dissipation at $T_A=25^{\circ}\text{C}^{(b)}$	P_D	1.4	W
Linear derating factor		11	mW/ $^{\circ}\text{C}$
Operating and storage temperature range	T_j, T_{stg}	-55 to 150	$^{\circ}\text{C}$

Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	$R_{\theta JA}$	131	$^{\circ}\text{C/W}$
Junction to ambient ^(b)	$R_{\theta JA}$	89	$^{\circ}\text{C/W}$
Junction to lead ^(d)	$R_{\theta JL}$	68	$^{\circ}\text{C/W}$

NOTES:

- (a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- (b) For a device surface mounted on FR4 PCB measured at $t \leq 5$ sec.
- (c) Repetitive rating - 25mm x 25mm FR4 PCB, $D=0.02$, pulse width 300 μs - pulse width limited by maximum junction temperature.
- (d) Thermal resistance from junction to solder-point (at end of drain lead).

Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	20			V	I _D = 250μA, V _{GS} =0V
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	V _{DS} = 20V, V _{GS} =0V
Gate-Body Leakage	I _{GSS}			100	nA	V _{GS} =±12V, V _{DS} =0V
Gate-Source Threshold Voltage	V _{GS(th)}	0.5	0.8	1.5	V	I _D = 250μA, V _{DS} =V _{GS}
Static Drain-Source On-State Resistance (*)	R _{DS(on)}			0.060 0.120	Ω Ω	V _{GS} = 4.5V, I _D = 2.5A V _{GS} = 2.5V, I _D = 1.0A
Forward Transconductance ^(*) (†)	g _{fs}		7.5		S	V _{DS} = 10V, I _D = 2.5A
Dynamic (†)						
Input Capacitance	C _{iss}		277		pF	V _{DS} = 10V, V _{GS} =0V f=1MHz
Output Capacitance	C _{oss}		65		pF	
Reverse Transfer Capacitance	C _{rss}		35		pF	
Switching (‡)(†)						
Turn-On-Delay Time	t _{d(on)}		2.65		ns	V _{DD} = 10V, V _{GS} = 4.5V I _D = 1A R _G ≈ 6.0Ω
Rise Time	t _r		4.2		ns	
Turn-Off Delay Time	t _{d(off)}		9.9		ns	
Fall Time	t _f		5.1		ns	
Total Gate Charge	Q _g		2.8		nC	V _{DS} = 10V, V _{GS} = 4.5V I _D = 2.5A
Gate-Source Charge	Q _{gs}		0.61		nC	
Gate Drain Charge	Q _{gd}		0.63		nC	
Source-drain diode						
Diode Forward Voltage ^(*)	V _{SD}		0.73	1.2	V	I _S = 1.25A, V _{GS} =0V
Reverse recovery time ^(†)	t _{rr}		6.5		ns	T _j =25°C, I _F =1.65A di/dt=100A/μs
Reverse recovery charge ^(†)	Q _{rr}		1.4		nC	

NOTES:

(*) Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

(†) For design aid only, not subject to production testing.

(‡) Switching characteristics are independent of operating junction temperature.